

Title (en)

Method for manufacturing thin semiconductor chips

Title (de)

Verfahren zur Herstellung von dünnen Halbleiterchips

Title (fr)

Méthode de production de puces semiconductrices minces

Publication

EP 1091394 A3 20020109 (EN)

Application

EP 00121597 A 20001002

Priority

JP 28313999 A 19991004

Abstract (en)

[origin: EP1091394A2] In a process of manufacturing semiconductor chips (C), first, the reverse of a wafer (W), on the obverse of which many chips (C) are formed, is ground so as to shape the wafer (W) with a predetermined thickness. Then, the reverse of the wafer (W) is polished or etched so that the broken layer which is formed during the back grinding is removed. Next, grooves (G) are formed on the obverse of the wafer (W) in a predetermined depth along streets (S) formed between the chips (C). Finally, the wafer (W) is cleft along the grooves (G) so as to be divided into separate chips (C). By this process, the broken layer formed on the reverse of the wafer (W) is removed after the back grinding, then the wafer (W) is divided into separate chips (C) by use of the cleavage; therefore, chipping is effectively reduced. <IMAGE>

IPC 1-7

H01L 21/304; H01L 21/78; H01L 21/306

IPC 8 full level

H01L 21/304 (2006.01); **H01L 21/301** (2006.01); **H01L 21/78** (2006.01)

CPC (source: EP KR)

H01L 21/304 (2013.01 - KR); **H01L 21/78** (2013.01 - EP)

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